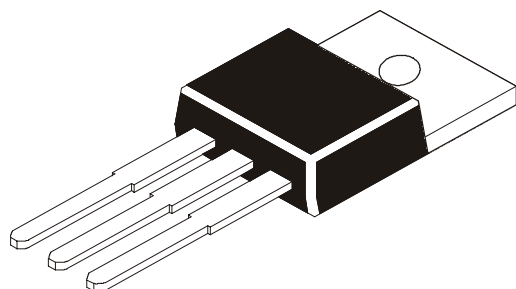


PNP SILICON EPITAXIAL POWER TRANSISTOR

CSB1370
(9AW)
TO-220



MARKING : AS BELOW

Designed For AF Power Amplifier.

ABSOLUTE MAXIMUM RATINGS(Ta=25deg C)

DESCRIPTION	SYMBOL	VALUE	UNIT
Collector -Base Voltage	VCBO	60	V
Collector -Emitter Voltage	VCEO	60	V
Emitter- Base Voltage	VEBO	5.0	V
Collector Current	IC	3.0	A
Peak	ICP	6.0	A
Power Dissipation @ Ta=25 deg C	PC	2.0	W
Power Dissipation @ Tc=25 deg C		30	W
Junction Temperature	Tj	150	deg C
Storage Temperature Range	Tstg	-55 to +150	deg C

ELECTRICAL CHARACTERISTICS (Ta=25 deg C Unless Specified)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Collector Emitter Voltage	VCEO	IC=1mA, IB=0	60	-	-	V
Collector Base Voltage	VCBO	IC=50uA, IE=0	60	-	-	V
Emitter Base Voltage	VEBO	IE=50uA, IC=0	5.0	-	-	V
Collector Cut off Current	ICBO	VCB=60V, IE=0	-	-	10	uA
Emitter Cut off Current	IEBO	VEB=4V, IC=0	-	-	10	uA
Collector Emitter Saturation Voltage	VCE(Sat)	IC=2A, IB=0.2A	-	-	1.5	V
Base Emitter Saturation Voltage	VBE(Sat)	IC=2A, IB=0.2A	-	-	1.5	V
DC Current Gain	hFE	IC=0.5A, VCE=5V	60	-	320	
Dynamic Characteristics						
Transition Frequency	ft	VCE=5V, IC=0.5A, f=5MHz	-	15	-	MHz
Collector Output Capacitance	Cob	VCB=10V, IE=0 f=1MHz	-	80	-	pF

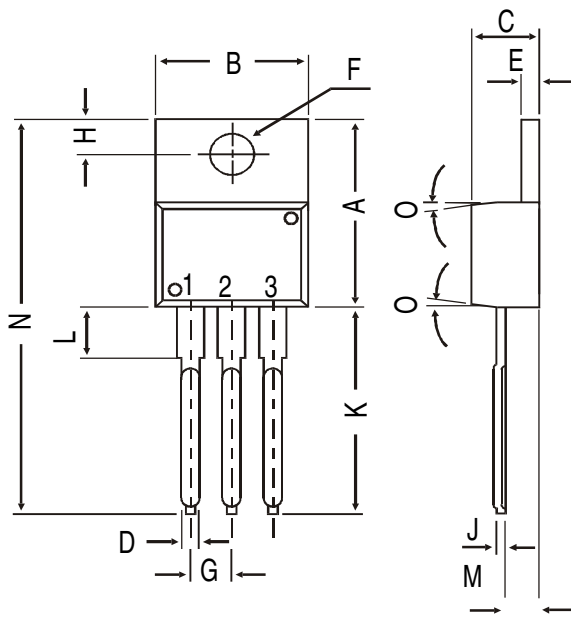
hFE CLASSIFICATION:-

D : 60 -120; E : 100 -200 F : 160 -320

MARKING :

CSB CSB CSB
1370 1370 1370
D E F

TO-220 Plastic Package

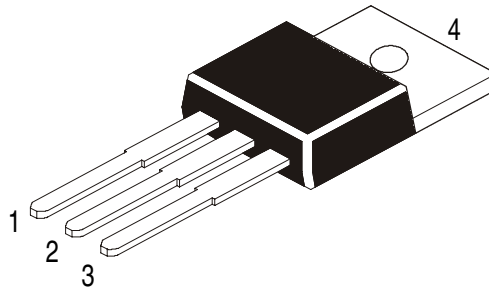


All dimensions in mm.

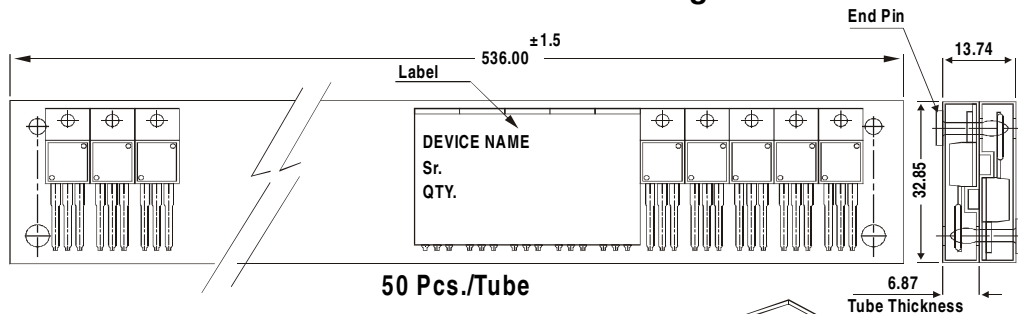
DIM	MIN.	MAX.
A	14.42	16.51
B	9.63	10.67
C	3.56	4.83
D	—	0.90
E	1.15	1.40
F	3.75	3.88
G	2.29	2.79
H	2.54	3.43
J	—	0.56
K	12.70	14.73
L	2.80	4.07
M	2.03	2.92
N	—	31.24
O	DEG 7	

PIN CONFIGURATION

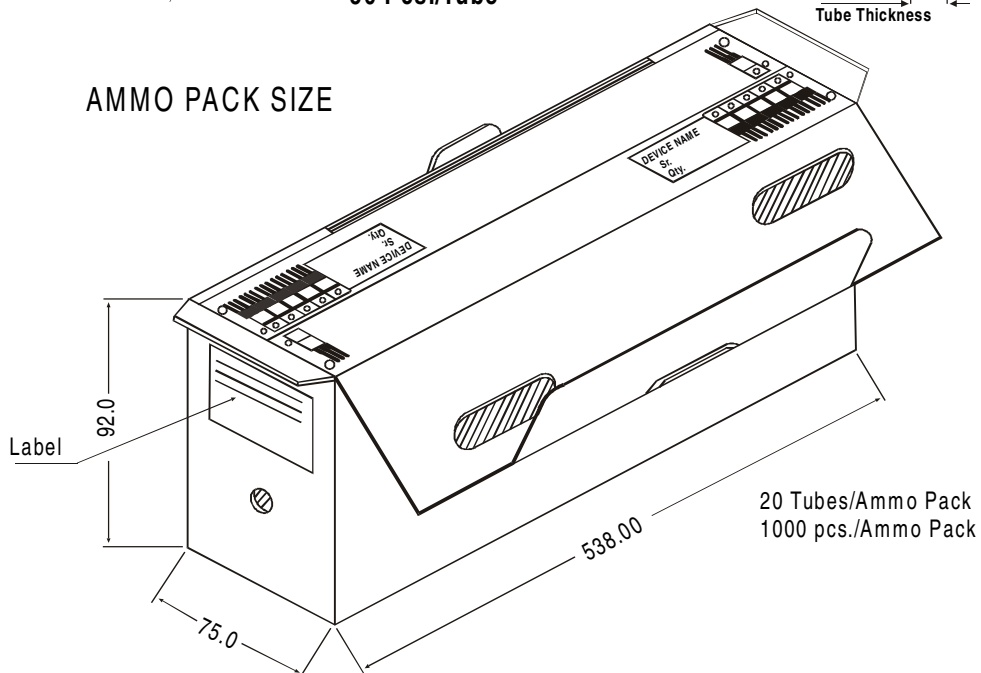
1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR



TO-220 Tube Packing



AMMO PACK SIZE



Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-220 / FP	200 pcs/polybag	396 gm/200 pcs	3" x 7.5" x 7.5"	1.0K	17" x 15" x 13.5"	16.0K	36 kgs
	50 pcs/tube	120 gm/50 pcs	3.5" x 3.7" x 21.5"	1.0K	19" x 19" x 19"	10.0K	29 kgs

Notes

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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